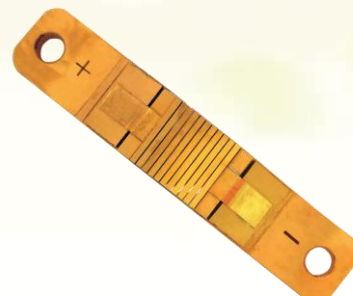


808nm G-Stack Stack

Introduction

Adopting AuSn welding package to achieve higher reliable ,longer lifespan and consecutive high power output. Laser Diode G-Stack Array is widely applied in laser pumping, cutting and laser medical, etc.

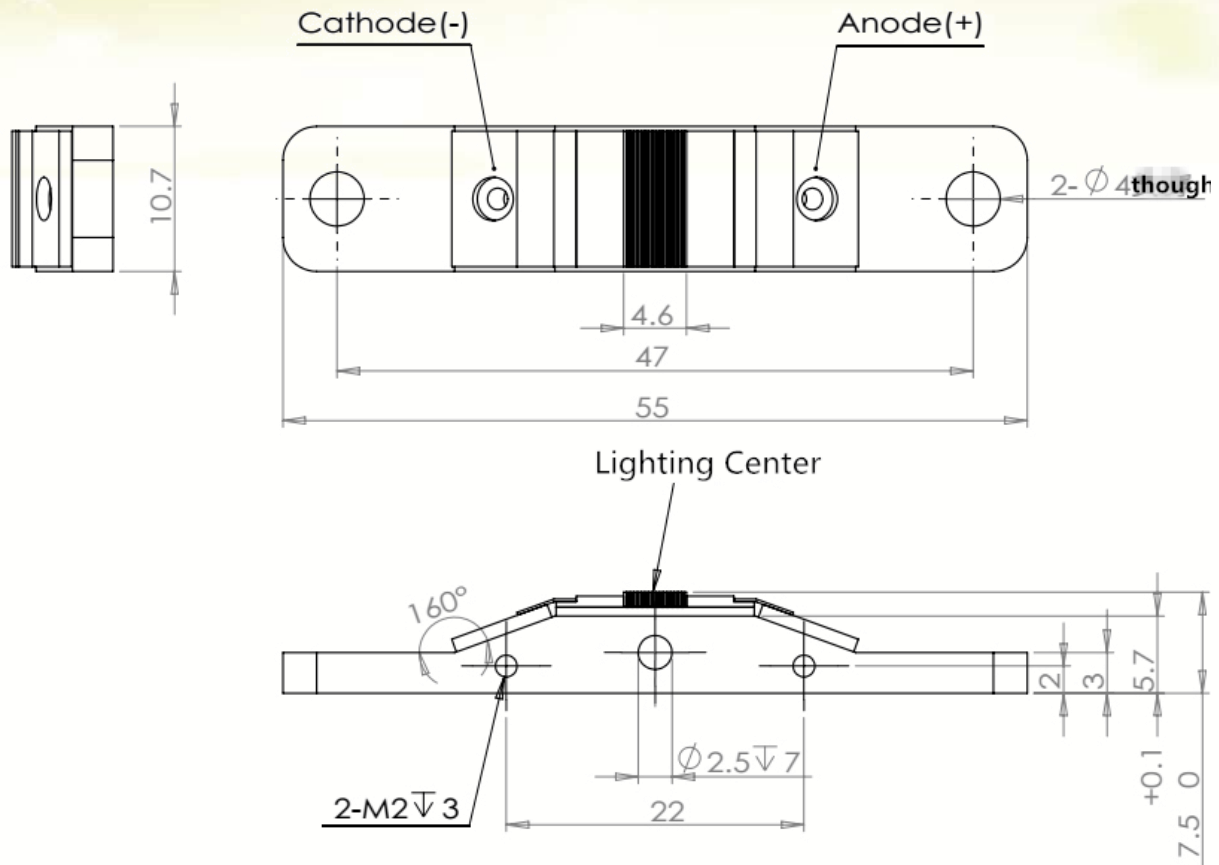


Parameters (25°C)

G-Stack Array					
Parameter		Unit	LDAQ2-0808-****		
Optical Parameter	Operation Model	-	QCW		
	Center Wavelength	nm	808 ± 5		
	Output Power/Bar	W	100	200	300
	Bar Qty.	bar	4~20		
	Bar Space	mm	0.4/0.8/1.2		
	Spectral Width	nm	< 5		
	Wavelength & Temperature Ratio	nm/°C	0.28		
	Fast Axis Divergence	deg	< 35		
	Slow Axis Divergence	deg	< 10		
Electrical Parameter	Duty Ratio	%	≤ 3	≤ 4	≤ 4
	Threshold Current	A	< 22	< 20	< 20
	Operating Current	A	< 120	< 230	< 295
Thermal Parameter	Operating Voltage	V	< 2.1	< 2.4	< 2.4
	Operating Temperature	°C	15 ~ 35		
	Storage Temperature	°C	-10 ~ 60		



Package



Notice

1. Item model notice: LDAQ2(item model)-8080(center wavelength)-****(output power)
2. Package data is only for reference, which can be customized as client's design drawing.
3. Please make sure laser diode is operated within 15-35°C, as higher temperature will cause increased threshold current, lower exchange rate and accelerate the aging.
4. Please take measure to avoid of condensation, which will cause aging of laser diode.
5. For more information, please contact Hi-Tech Optoelectronics Co., Ltd.

